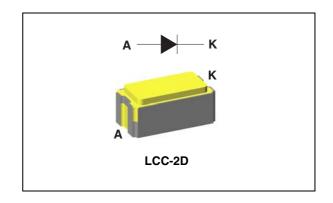


# Aerospace 0.3 A - 100 V switching diode

#### **Features**

- Surface mount hermetic package
- High thermal conductivity materials
- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop
- Target radiation qualification:
  - 150 krad (Si) low dose rate
  - 3 Mrad high dose rate
- Package weight: 0.12 g



#### **Description**

This power ultrafast recovery rectifier is designed and packaged to comply with the ESCC5000 specification for aerospace products. It is housed in a surface mount hermetically sealed LCC-2D package whose footprint is 100% compatible with industry standard solutions in D5A.

The 1N6642U is suitable for switching mode power supplies and high frequency DC to DC converters such as low voltage high frequency inverter, free wheeling or polarity protection.

Table 1. Device summary<sup>(1)</sup>

| Order code | ESCC detailed specification | Quality level        | EPPL | I <sub>F(AV)</sub> | V <sub>RRM</sub> | T <sub>j(max)</sub> | V <sub>F (max)</sub> |
|------------|-----------------------------|----------------------|------|--------------------|------------------|---------------------|----------------------|
| 1N6642UD1  | -                           | Engineering<br>model | -    | 0.3 A              | 100 V            | 175 °C              | 1.2 V                |
| 1N6642U02D | 5101/026/xx                 | Flight part Target   |      |                    |                  |                     |                      |

<sup>1.</sup> Contact ST sales office for information about the specific conditions for products in die form and gold plated version.

Characteristics 1N6642U

### 1 Characteristics

Table 2. Absolute ratings (limiting values)

| Symbol              | Parameter  | Value       | Unit |   |
|---------------------|--|-------------|------|---|
| $V_{RRM}$           | Repetitive peak reverse voltage  | 100         | V    |   |
| I <sub>F(RMS)</sub> | Forward rms current  |             | 0.5  | Α |
| I <sub>F(AV)</sub>  | Average forward rectified current (1)  | 300         | mA   |   |
| I <sub>FSM</sub>    | Forward surge current $ \begin{aligned} t_p = 8.3 \text{ ms sinusoidal,} \\ t_{amb} \leq 25 \text{ °C} \end{aligned} $ |             | 2    | А |
| T <sub>stg</sub>    | Storage temperature range  | -65 to +175 | °C   |   |
| T <sub>j</sub>      | Operating junction temperature range   | -65 to +175 | °C   |   |
| T <sub>sol</sub>    | Maximum soldering temperature (2)  | 245         | °C   |   |

<sup>1.</sup> For all variants at T  $_{\!c} \geq$  +155  $^{\circ}\text{C}$  per diode, derate linearly to 0 A at +175  $^{\circ}\text{C}.$ 

Table 3. Thermal resistance

| Symbol                | Parameter            | Value | Unit  |
|-----------------------|----------------------|-------|-------|
| R <sub>th (j-c)</sub> | Junction to case (1) | 60    | °C/W  |
| R <sub>th (j-a)</sub> | Junction to ambient  | 280   | C/ VV |

<sup>1.</sup> Package mounted on infinite heatsink

Table 4. Static electrical characteristics

| Symbol                         | Parameter         | Tests conditions        |                         | Min. | Тур. | Max. | Unit  |
|--------------------------------|-------------------|-------------------------|-------------------------|------|------|------|-------|
| V <sub>BR</sub> <sup>(1)</sup> | Breakdown voltage | T <sub>j</sub> = 25 °C  | I <sub>R</sub> = 100 μA | 100  | -    | -    | V     |
|                                | Reverse current   | T <sub>j</sub> = 25 °C  | V <sub>R</sub> = 20 V   | -    | -    | 25   | nA    |
| I <sub>R</sub> <sup>(1)</sup>  |                   | T <sub>j</sub> = 25 °C  | V <sub>R</sub> = 75 V   | -    | -    | 50   | nA    |
| 'R`                            |                   | T <sub>j</sub> = 150 °C | V <sub>R</sub> = 20 V   | -    | -    | 30   | μΑ    |
|                                |                   | T <sub>j</sub> = 150 °C | V <sub>R</sub> = 75 V   | -    | -    | 40   | μΑ    |
|                                | Forward voltage   | T <sub>j</sub> = 25 °C  | I <sub>F</sub> = 10 mA  | -    | -    | 800  |       |
| V <sub>F</sub> <sup>(2)</sup>  |                   | T <sub>j</sub> = 25 °C  | I <sub>F</sub> = 100 mA | -    | -    | 1200 | mV    |
|                                |                   | T <sub>j</sub> = 150 °C | I <sub>F</sub> = 10 mA  | -    | -    | 800  | 111.0 |
|                                |                   | T <sub>j</sub> = -55 °C | I <sub>F</sub> = 100 mA | -    | -    | 1200 |       |

<sup>1.</sup> Pulse test: tp = 10 ms,  $\delta$  < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.74 \times I_{F(AV)} + 1.00 \times I_{F}^{2}(RMS)$$

<sup>2.</sup> Maximum duration 5 s. The same package must not be re-soldered until 3 minutes have elapsed.

<sup>2.</sup> Pulse test: tp = 680  $\mu$ s,  $\delta$  < 2%

1N6642U Characteristics

Table 5. Dynamic characteristics

| Symbol          | Parameter                | Test conditions  | Min. | Тур. | Max. | Unit |  |
|-----------------|--------------------------|--|------|------|------|------|--|
| +               | Reverse recovery time    | $I_F = I_R = 10 \text{ mA}^{(1)}$  | -    | -    | 9    | ns   |  |
| t <sub>rr</sub> | Theverse recovery time   | $I_F = 1 \text{ A}, V_r = 30 \text{ V}, \text{ dI/dt} = -15 \text{ A/}\mu\text{s}$ |      |      | 20   | 113  |  |
| $V_{FP}$        | Forward recovery voltage | I <sub>FM</sub> = 200 mA   | -    | -    | 5    | V    |  |
| t <sub>FR</sub> | Forward recovery time    | I <sub>FM</sub> = 200 mA   | -    | -    | 20   | ns   |  |
| C <sub>j</sub>  | Diode capacitance        | V <sub>R</sub> = 0 V, V = 50 mV, F = 1 MHz   | -    | -    | 5    | pF   |  |
|                 |                          | V <sub>R</sub> = 1.5 V, V = 50 mV, F = 1 MHz                                       | -    | -    | 2.8  | pF   |  |

<sup>1.</sup> Guaranteed but not tested

Figure 1. Forward voltage drop versus forward current (typical values)

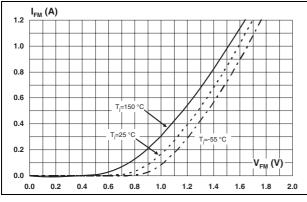
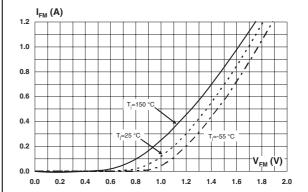


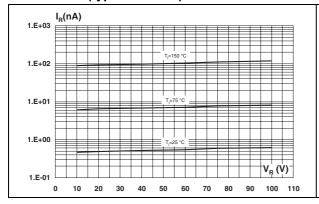
Figure 2. Forward voltage drop versus forward current (maximum values)



Characteristics 1N6642U

Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

Figure 4. Relative variation of thermal impedance, junction to case, versus pulse duration



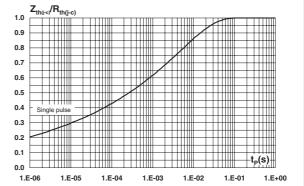
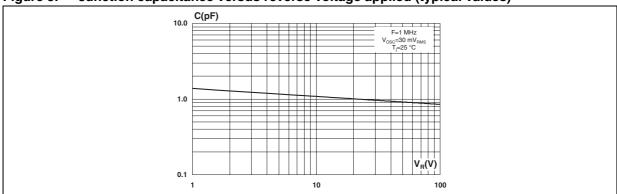


Figure 5. Junction capacitance versus reverse voltage applied (typical values)



1N6642U Package information

## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

**Dimensions** Ref. Millimeters Inches Min. Min. Max. Тур. Max. Тур.  $A^{(1)}$ 1.86 2.03 2.20 0.073 0.080 0.087 4.57 0.180 0.188 В 4.44 4.77 0.175 С 2.10 0.072 0.078 0.083 1.84 1.97 0.060 0.067 0.074 D 1.53 1.70 1.87 0.71 0.019 0.028 Ε 0.48 F 0.051 1.3 G 0.066 1.67 Н 0.37 0.015 0.15 0.006 0.15 0.006 r1 r2 0.20 0.008 Note 1: The anode is identified by metallization in two top internal angles and the index mark.

Table 6. Leadless chip carrier 2 (LCC-2D) package dimensions

<sup>1.</sup> Measurement prior to solder coating the mounting pads on bottom of package

Ordering information 1N6642U

## 3 Ordering information

Table 7. Ordering information<sup>(1)</sup>

| Order code | ESCC detailed specification | Package | Lead finish | Marking | EPPL   | Weight | Packing |
|------------|-----------------------------|---------|-------------|---------|--------|--------|---------|
| 1N6642UD1  | -                           | LCC-2D  | Gold        | 42UD1   | -      | 0.12 g | Waffle  |
| 1N6642U02D | 5101/026/xx                 | 100-20  | Solder dip  | 42U02D  | Target | 0.12 g | pack    |

Contact ST sales office for information about the specific conditions for products in die form and gold plated version.

## 4 Revision history

Table 8. Document revision history

| Date        | Revision | Changes                                     |  |  |
|-------------|----------|---|--|--|
| 26-Mar-2010 | 1        | First issue.                                |  |  |
| 23-Sep-2011 | 2        | Updated order codes in Table 1 and Table 7. |  |  |

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